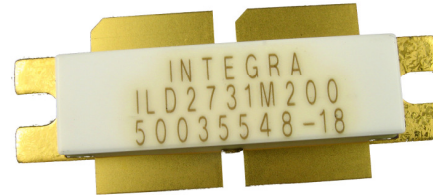


### S-Band Radar Transistor

Part number ILD2731M200 is designed for S-Band radar applications operating over the 2.7 – 3.1 GHz instantaneous frequency band. Under 300us / 10% pulsing conditions it supplies a minimum of 200 watts of peak output power with 11dB gain typically. Specified operation is with Class AB bias. The single-ended broadband test fixture includes a temperature compensated bias network. All devices are 100% screened for large signal RF parameters in a fixed tuned broadband matching circuit / test fixture. The use of external tuners is not allowed during screening.



#### Silicon LDMOS FET

- High Power Gain
- Excellent thermal stability
- Gold Metal

#### Gold Metal System

- Complete Gold System
- LDMOS with Gold Metal
- Gold Bond Wires
- Gold Package Metal
- Maximum Reliability

#### Class AB Operation

- Specified with AB bias

#### Internal Impedance Matching

- Ease of Use
- Ultra Low Loss Design

#### BeO Free Package

- Metal Based
- Epoxy Seal

#### High Power RF Test / Fixture

- Single-ended
- Broadband
- Matched to 50  $\Omega$  (ohms)
- Temperature Compensated Bias
- Long-term Correlation
- 100% Device RF Screening
- No External Tuning required

### TYPICAL DATA TYPICAL DATA TYPICAL DATA TYPICAL DATA

Freq (GHz)	PW ( $\mu$ S)	Duty (%)	Pout (W)	IRL (dB)	Gp (dB)	Id (A)	Nd (%)	Droop (dB)	VSWR-S (3:1)
TBD									

**MAXIMUM RATINGS**

Screen	Parameter	Symbol	Min	Max	Units	Test Conditions
BD	Drain-Source Voltage	$V_{DS}$	--	65	V	--
BD	Gate-Source Voltage	$V_{GS}$	-0.5	12	V	--
BD	Storage Temperature Range	$T_{STG}$	-55	+200	°C	--
BD	Operating Junction Temperature Range	$T_J$	-55	+200	°C	--
Note	Screen 'BD' = parameter qualified By Design.					

**THERMAL CHARACTERISTICS**

Screen	Parameter	Symbol	Min	Max	Units	Test Conditions
BD	Thermal Resistance	$R_{TH(JC)}$	--	0.13	°C/W	$V_{DD}=V1, I_{DQ}=I_{DQ1}, PW=PW1, DF=DF1, T_F=25\pm5^\circ C, P_{OUT}=200W, N_D=35\%$
Note	Screen 'BD' = parameter qualified By Design.					

**PROCESSING SPECIFICATIONS**

Screen	Parameter	Symbol	Min	Max	Units	Test Conditions
100%	DC Wafer Probe	--	--	--	--	Per Integra specification.
Q1	Wafer DC and RF Qualification	--	--	--	--	Per Integra specification.
LM	Wire Bond Strength	--	--	--	--	Line monitor per Integra specification.
100%	Pre-cap visual inspection	--	--	--	--	Per Integra specification
100%	Gross leak test	--	--	--	--	MIL-STD-750D, Method 1071.6, Test Condition C
Note	Screen 'Q1' = parameter is qualified by assembly and test of 3 pieces minimum per wafer.					
Note	Screen 'LM' = parameter is qualified by assembly line monitor.					



**DC ELECTRICAL CHARACTERISTICS**

Screen	Parameter	Symbol	Min	Max	Units	Test Conditions
100%	Drain-Source Breakdown Voltage	$BV_{DSS}$	65	--	V	$I_{DS}=15mA, V_{GS}=0V, T_F=25\pm5^\circ C$
BD	Drain Leakage Current	$I_{DSS}$	--	1.5	uA	$V_{DS}=32V, V_{GS}=0V, T_F=25\pm5^\circ C$
100%	Operating Gate Voltage	$V_{GS}$	2.0	4.0	V	$V_{DS}=5V, I_D=0.15A, T_F=25\pm5^\circ C$
BD	Gate Leakage Current	$I_{GSS}$	--	1.5	uA	$V_{GS}=10V, V_{DS}=0V, T_F=25\pm5^\circ C$

**RF ELECTRICAL CHARACTERISTICS**

Screen	Parameter	Symbol	Min	Max	Units	Test Conditions
100%	Input Return Loss	IRL	-18	-7	dB	$V_{DD}=V1, I_{DQ}=I_{DQ1}, PW=PW1, DF=DF1, T_F=T_{F1}, P_{OUT}=P_{OUT1}, F=F1, F2, F3.$
100%	Pout	Po	200	260	dB	$V_{DD}=V1, I_{DQ}=I_{DQ1}, PW=PW1, DF=DF1, T_F=T_{F1}, P_{OUT}=P_{OUT1}, F=F1, F2, F3.$
100%	Power Gain	dB	10.8	12.04	dB	$V_{DD}=V1, I_{DQ}=I_{DQ1}, PW=PW1, DF=DF1, T_F=T_{F1}, P_{OUT}=P_{OUT1}, F=F1, F2, F3.$
100%	Drain Efficiency	$\eta_D$	35	50	%	$V_{DD}=V1, I_{DQ}=I_{DQ1}, PW=PW1, DF=DF1, T_F=T_{F1}, P_{OUT}=P_{OUT1}, F=F1, F2, F3.$
100%	Pulse Amplitude Droop	D	-0.5	+0.5	dB	$V_{DD}=V1, I_{DQ}=I_{DQ1}, PW=PW1, DF=DF1, T_F=T_{F1}, P_{OUT}=P_{OUT1}, F=F1, F2, F3.$
100%	3:1 Load Mismatch Stability	VSWR-S	Pass	--	P/F	$V_{DD}=V1, I_{DQ}=I_{DQ1}, PW=PW1, DF=DF1, T_F=T_{F1}, P_{OUT}=P_{OUT1}, F=F1, F2, F3.$ Rotate 3:1 output VSWR through 360° phase. No oscillatory or pulse break-up characteristics allowed on detected output pulse. All non-harmonically related signals must be at least -65 dBc.
Note 1	$V1 = 32V; I_{DQ1} = 60mA; PW1 = 300\mu s; DF1 = 10\%, P_{OUT1} = 200W \text{ Peak}, 20W \text{ Ave}$					
Note 2	Test Frequencies: $F1 = 2.7 \text{ GHz}, F2 = 2.9 \text{ GHz}, F3 = 3.1 \text{ GHz}.$					
Note 3	$T_{F1} = 25\pm 5^\circ C = \text{Device flange temperature}.$					
Note 4	Screen 'BD' = parameter qualified By Design.					

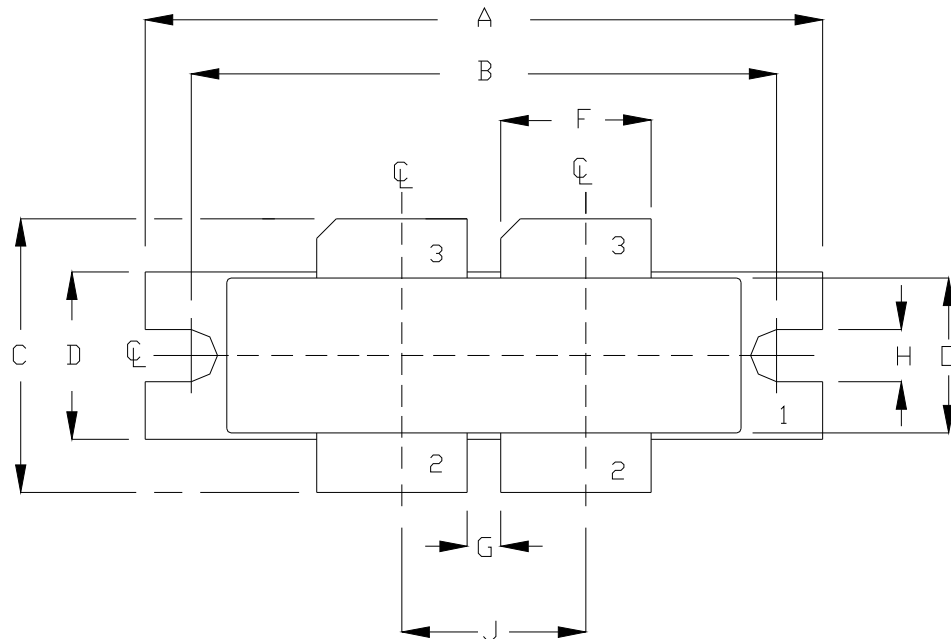
**RF TEST FIXTURE IMPEDANCE CHARACTERISTICS**

Frequency (GHz)	$Z_{IF} (\Omega)$	$Z_{OF} (\Omega)$
2.70	TBD	TBD
2.90	TBD	TBD
3.10	TBD	TBD
Impedance Definition		

PERFORMANCE GRAPHS (Pout=200W except as noted)

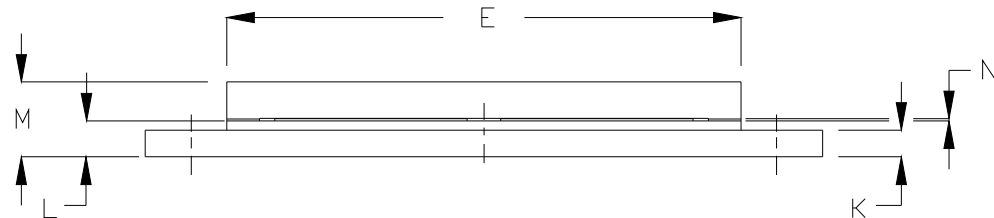
**TBD**

**PACKAGE DIMENSIONAL OUTLINE DRAWING**

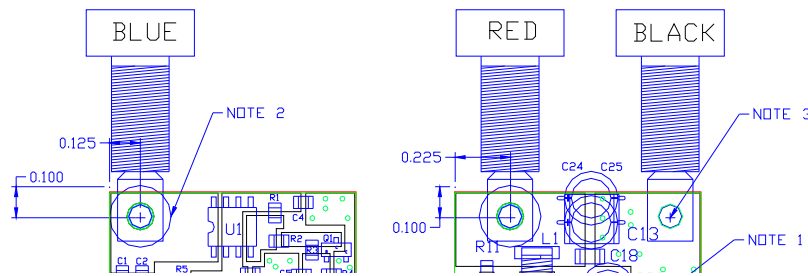


DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	1.615	1.625	41.02	41.27
B	1.395	1.405	35.43	35.69
C	0.634	0.674	16.10	17.12
D	0.395	0.405	10.03	10.29
E	1.219	1.241	30.96	31.52
F	0.355	0.365	9.02	9.27
G	0.075	0.085	1.90	2.16
H	0.120	0.130	3.05	3.30
J	0.435	0.445	11.05	11.30
K	0.059	0.069	14.99	17.53
L	0.081	0.091	2.06	2.31
M	0.164	0.194	4.16	4.93
N	0.004	0.007	0.10	0.18
□	0.354	0.364	8.99	9.24

PIN SCHEDULE	
1	SOURCE
2	GATE
3	DRAIN



**RF TEST FIXTURE – ASSEMBLY AND PARTS LIST**

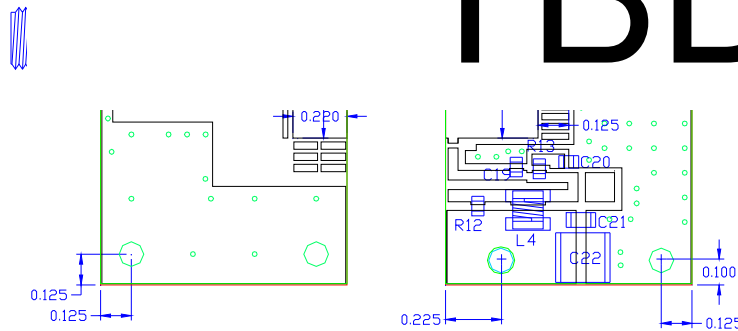


**PARTS LIST**

PC Board Type: ROGERS RD4350B-03011, 30mil,  
1/1oz. Copper  
Aluminum Heatsink: RPK005 ILD501 HEATSINK  
Input PC Board Carrier: -3 (1")  
Output PC Board Carrier: -3 (1")  
Transistor Copper Carrier: RPK-003B-003  
RF connector: DS #2052-5636-02  
Ground: Plated thru vias (OR GND STRAPS PER  
BELOW)  
Banana jack Black -1 places  
Banana jack Blue - 1 place  
Banana jack Red -1 places  
C7,C16,C18: CAP 5245 ATC 500ER04 50G MNT.,  
VT.

**TBD**

\*IC CAP  
CAP



R5: RES,4.7K,0805  
R8: RES,1.5K,0805  
R7,R9,R10,R11,R12,R13: RES,5R1,0805  
R6: RES,VAR,2K,4MM,3224W,BOURNS

NOTES  
1)GS1-GS23: GROUND STRAP, FOLD AS SHOWN. GS  
CAN BE USED INSTEAD OF PLATED VIAS.  
2)SHOULDER WASHER KEYSTONE #3229 ON  
RED/BLUE JACKS. NO WASHER NEEDED ON BLACK.  
3)JACKS SCREWED IN WITH 2-56 SCREWS

**CONTACT FACTORY FOR RF TEST FIXTURE CAD DRAWING WITH CIRCUIT DIMENSION**

**L:\Public\Controlled Documents\Controlled Drawings\RF Test Fixture Drawings\ILD2731M200**

**RF TEST FIXTURE REV NC.dwg**

**DEFINITIONS**

<b>Data Sheet Status</b>	
Proposed Specification	This data sheet contains proposed specifications.
Preliminary Specification	This data sheet contains specifications based on preliminary measurements and data.
Product Specification	This data sheet contains final product specifications.
<b>Maximum Ratings</b>	
Stress above one or more of the maximum ratings may cause permanent damage to the device. These are maximum ratings only operation of the device at these or at any other conditions above those given in the characteristics sections of the specification is not implied. Exposure to maximum values for extended periods of time may affect device reliability.	

**WARNING**

<b>Product and environmental safety - toxic materials</b>
This product contains beryllium oxide. The product is entirely safe provided that the BeO base is not damaged. All persons who handle, use or dispose of this product should be aware of its nature and of the necessary safety precautions. After use, dispose of as chemical or special waste according to the regulations applying at the location of the user. It must never be thrown out with general or domestic waste.

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